

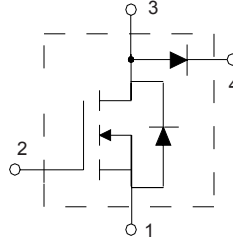
PolarHV™ HiPerFET IXFN 64N50PD2

Power MOSFET

Boost Configuration for PFC Circuits

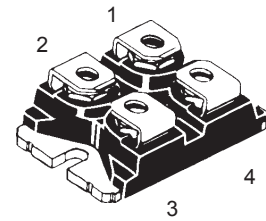
$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 52 \text{ A} \\ R_{DS(on)} &\leq 85 \text{ m}\Omega \\ t_{rr} &\leq 200 \text{ ns} \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	52	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	200	A
I_{AR}	$T_C = 25^\circ\text{C}$	36	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	625	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_D	Mounting Ttorque Terminal connection torque	1.5 / 13 5 / 13	Nm/lb-in Nm/lb-in
Weight		30	g

miniBLOC, SOT-227 B (IXFN)
E153432



1 = Source
2 = Gate
3 = Drain / Diode anode
4 = Diode / Diode cathode

Features

- Fast intrinsic diode in boost configuration
- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- Tightly coupled FRED diode
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 500 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			50 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 32 \text{ A}$, Note 1			85 m Ω

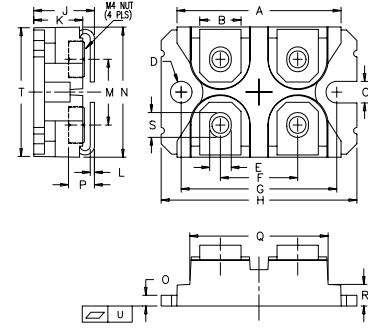
Symbol	Test Conditions	Characteristic Values (T _J = 25°C unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20 V; I _D = 32 A, Note 1	65	72	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		11	nF
C_{oss}			1020	pF
C_{rss}			80	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 64 A R _G = 2 Ω (External)		28	ns
t_r			32	ns
t_{d(off)}			110	ns
t_f			30	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 32 A		186	nC
Q_{gs}			60	nC
Q_{gd}			62	nC
R_{thJC}		0.05		0.2 °C/W
R_{thCS}				°C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T _J = 25°C unless otherwise specified)		
		Min.	Typ.	Max.
I_S	V _{GS} = 0 V			64 A
I_{SM}	Repetitive			200 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Note 1			1.5 V
t_{rr}	I _F = 25 A, -di/dt = 100 A/μs V _R = 100 V, V _{GS} = 0 V		0.8	200 ns
Q_{RM}				μC
I_{RM}				A

Note 1: Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %

SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2